

## General Description

The AO8804 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V  $V_{GS(MAX)}$  rating. It is ESD protected.

This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.

## Features

$V_{DS}$  (V) = 20V

$I_D$  = 8A

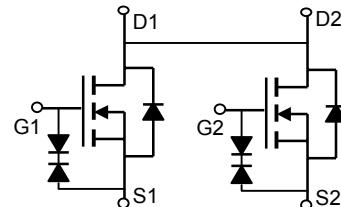
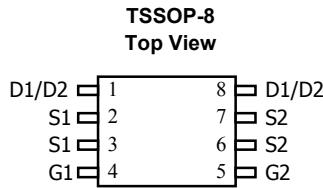
$R_{DS(ON)} < 13m\Omega$  ( $V_{GS} = 10V$ )

$R_{DS(ON)} < 14m\Omega$  ( $V_{GS} = 4.5V$ )

$R_{DS(ON)} < 19m\Omega$  ( $V_{GS} = 2.5V$ )

$R_{DS(ON)} < 27m\Omega$  ( $V_{GS} = 1.8V$ )

ESD Rating: 2000V HBM



### Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current <sup>A</sup>	$I_D$	8	A
$T_A=70^\circ C$		6.3	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$P_D$	1.5	W
$T_A=70^\circ C$		1.08	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C

### Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	64	83	°C/W
Steady-State		89	120	°C/W
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	53	70	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}, V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			10 25	$\mu\text{A}$
$I_{\text{GSS}}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 10\text{V}$			10	$\mu\text{A}$
$\text{BV}_{\text{GSO}}$	Gate-Source Breakdown Voltage	$V_{DS}=0\text{V}, I_G=\pm 250\mu\text{A}$	$\pm 12$			V
$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.5	0.75	1	V
$I_{\text{D(ON)}}$	On state drain current	$V_{GS}=4.5\text{V}, V_{DS}=5\text{V}$	30			A
$R_{\text{DS(ON)}}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=8\text{A}$ $T_J=125^\circ\text{C}$		10 13.3 16		$\text{m}\Omega$
		$V_{GS}=4.5\text{V}, I_D=5\text{A}$		11.5	14	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_D=4\text{A}$		15.4	19	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}, I_D=3\text{A}$		22.2	27	$\text{m}\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{DS}=5\text{V}, I_D=8\text{A}$		36		S
$V_{\text{SD}}$	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.73	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.4	A
<b>DYNAMIC PARAMETERS</b>						
$C_{\text{iss}}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$		1810		$\text{pF}$
$C_{\text{oss}}$	Output Capacitance			232		$\text{pF}$
$C_{\text{rss}}$	Reverse Transfer Capacitance			200		$\text{pF}$
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		1.6		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=8\text{A}$		17.9		nC
$Q_{\text{gs}}$	Gate Source Charge			1.5		nC
$Q_{\text{gd}}$	Gate Drain Charge			4.7		nC
$t_{\text{D(on)}}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=10\text{V}, R_L=1.2\Omega, R_{\text{GEN}}=3\Omega$		2.5		ns
$t_r$	Turn-On Rise Time			7.2		ns
$t_{\text{D(off)}}$	Turn-Off Delay Time			49		ns
$t_f$	Turn-Off Fall Time			10.8		ns
$t_{\text{rr}}$	Body Diode Reverse Recovery Time	$I_F=8\text{A}, \text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		20.2		ns
$Q_{\text{rr}}$	Body Diode Reverse Recovery Charge	$I_F=8\text{A}, \text{d}I/\text{d}t=100\text{A}/\mu\text{s}$		8		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80  $\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

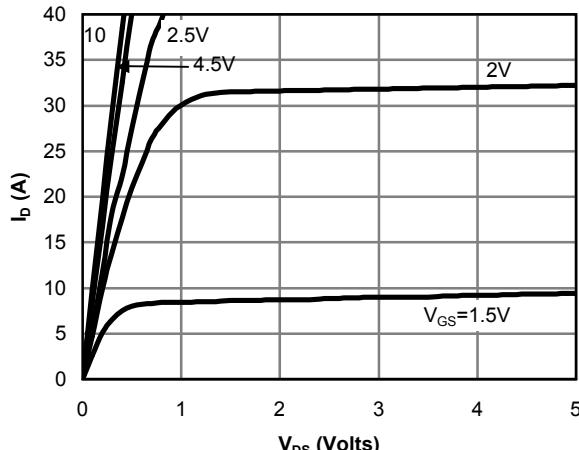


Fig 1: On-Region Characteristics

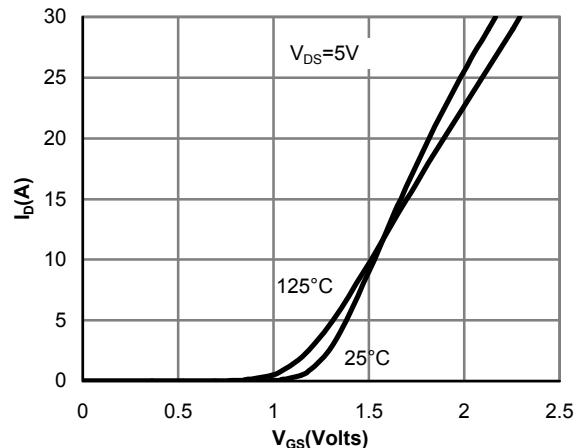


Figure 2: Transfer Characteristics

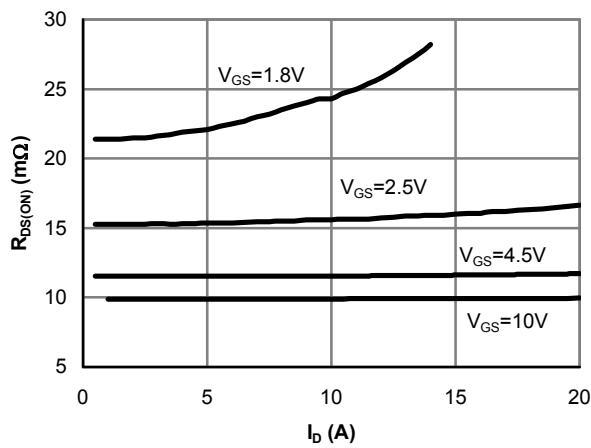


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

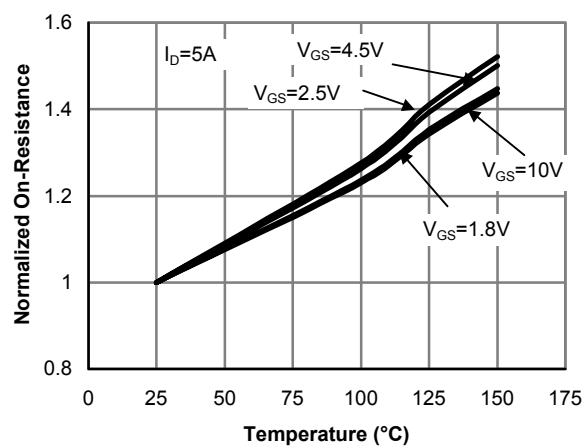


Figure 4: On-Resistance vs. Junction Temperature

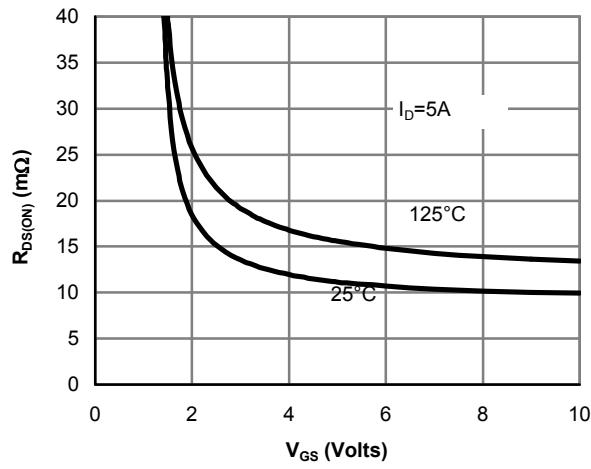


Figure 5: On-Resistance vs. Gate-Source Voltage

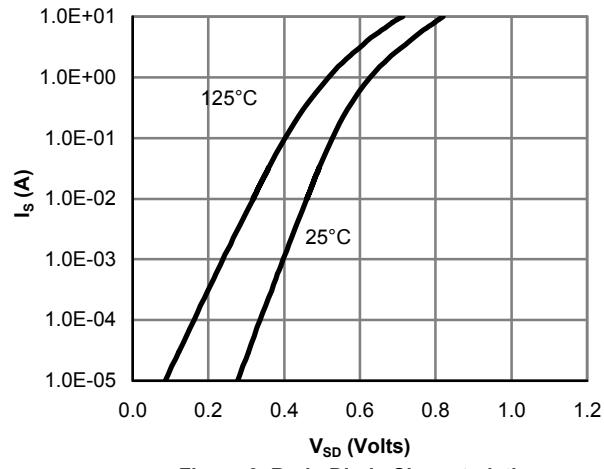


Figure 6: Body-Diode Characteristics

## TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

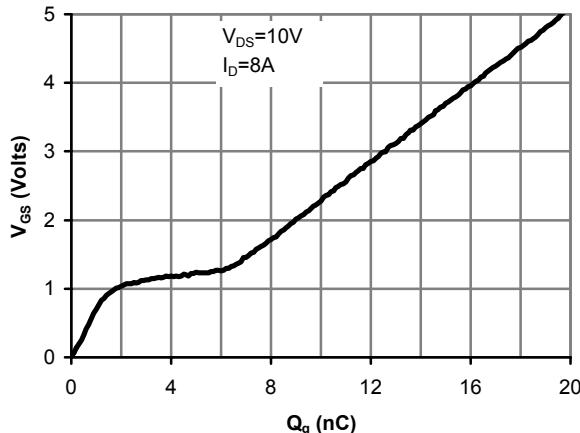


Figure 7: Gate-Charge Characteristics

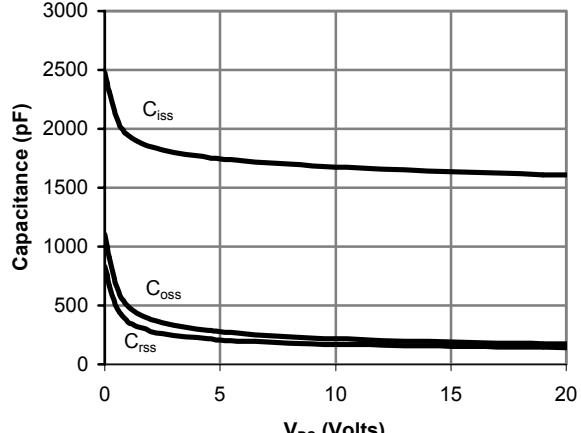


Figure 8: Capacitance Characteristics

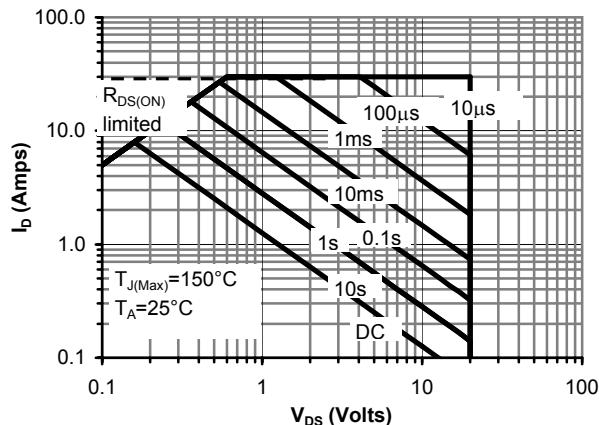


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

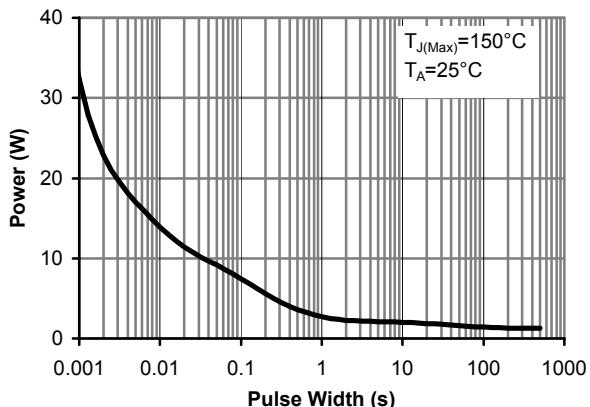


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

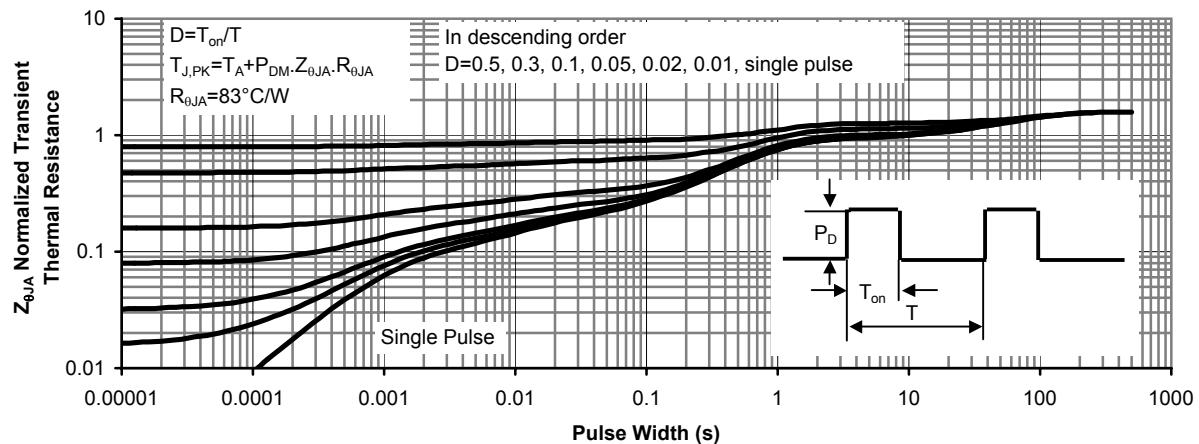
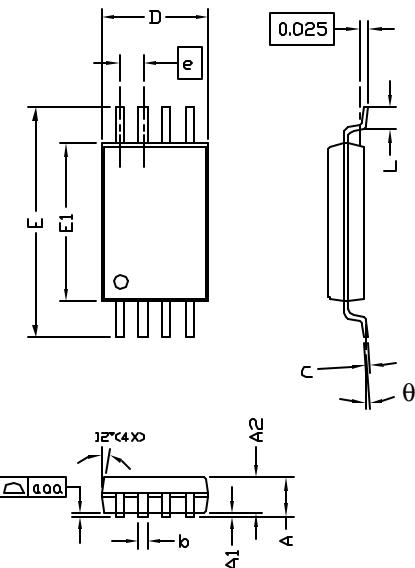


Figure 11: Normalized Maximum Transient Thermal Impedance



## TSSOP-8 Package Data

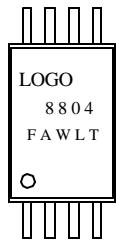


SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	—	—	1.20	—	—	0.047
A1	0.05	—	0.15	0.002	—	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19	—	0.30	0.007	—	0.012
c	0.09	—	0.20	0.004	—	0.008
D	2.90	3.00	3.10	0.114	0.118	0.122
E	6.40 BSC			0.252 BSC		
E1	4.30	4.40	4.50	0.169	0.173	0.177
e	0.65 BSC			0.0259 (REF)		
L	0.45	0.60	0.75	0.018	0.024	0.030
y	—	—	0.10	—	—	0.004
θ	0°	—	8°	0°	—	8°

NOTE:

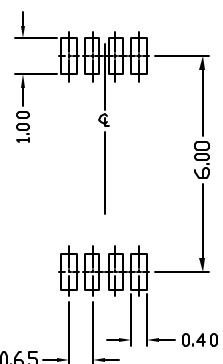
1. LEAD FINISH: 150 MICROINCHES (3.8  $\mu$ m) MIN.  
THICKNESS OF Tin/Lead (SOLDER) PLATED ON LEAD
2. TOLERANCE  $\pm 0.10$  mm (4 mil) UNLESS OTHERWISE SPECIFIED
3. COPLANARITY : 0.10 mm
4. DIMENSION L IS MEASURED IN GAGE PLANE

### PACKAGE MARKING DESCRIPTION



NOTE:  
 LOGO - AOS LOGO  
 8804 - PART NUMBER CODE.  
 F - FAB LOCATION  
 A - ASSEMBLY LOCATION  
 W - WEEK CODE.  
 L N - ASSEMBLY LOT CODE

### RECOMMENDED LAND PATTERN



UNIT: mm

### TSSOP-8 PART NO. CODE

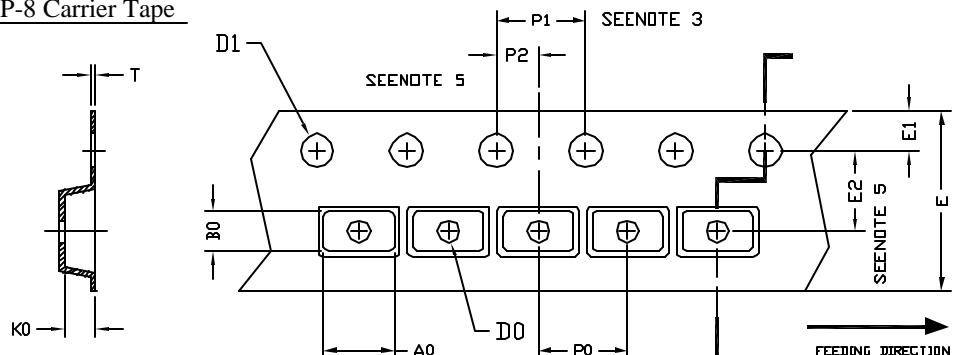
PART NO.	CODE
AO8804	8804

Rev.A



## TSSOP-8 Tape and Reel Data

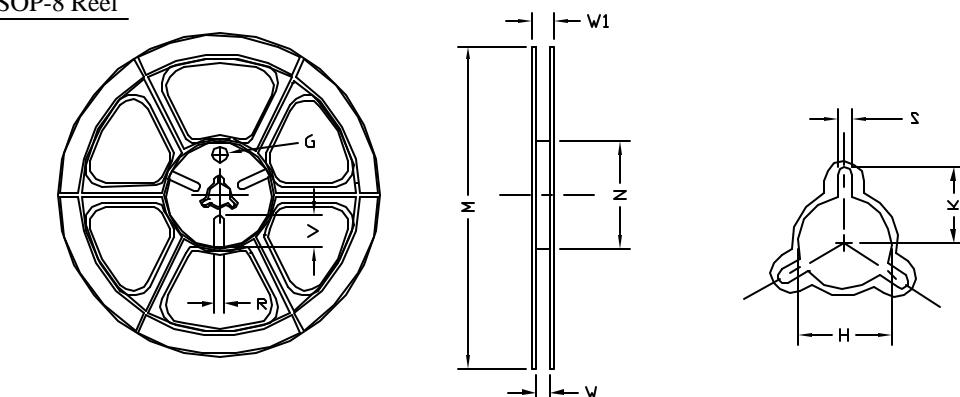
### TSSOP-8 Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SQ-8 (12 mm)	6.80 ±0.10	3.40 ±0.10	1.60 ±0.10	150 MIN.	1.50	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.10	0.30 ±0.05

### TSSOP-8 Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	Ø330	Ø178.00 ±0.50	Ø60.00 ±0.50	13.00 +1.50 -0.00	16.00 ±1.00	Ø13.50 ±0.50	10.60	220 ±0.50	---	---	---

### TSSOP-8 Tape

Leader / Trailer  
& Orientation

